

Page 21, third full paragraph, please replace with the following:

FIGS. 10A to 10D are illustrations showing the copper plate 56 to be employed for the semiconductor device 4 of the embodiment 2 of the present invention. FIG. 10A is a plane view, FIG. 10B is a cross-section cut along the line IX-IX' of FIG. 10A, FIG. 10C is a bottom face of FIG. 10B, and FIG. 10D is a cross-section cut along the line X-X' of FIG. 10A; and

FIGS. 11A to 11C are illustrations showing the copper plate 51 (example 1) to be employed for the semiconductor device 3 of the embodiment 1 of the present invention. FIG. 11A is a plane view, FIG. 11B is a cross-section cut along the line XI-XI' of FIG. 11A, and FIG. 11C is a bottom face of FIG. 11B.

Page 25, last paragraph (which bridges over to page 26, please replace it with the following:

As illustrated in FIGS. 4A and 4B, the copper plate 51 has dimples 53 in the upper face. The dimples 53 are those formed in the copper plate 51 and can be formed by etching and pressing. In the case of forming them by etching, they are formed by half etching, which is incompletely carried out etching. In the case where etching is completely carried out, the amount of copper removed is increased and the resistance value of the copper plate 51 is increased. In the case where the copper plate 51 has nothing to do with the resistance value, etching may completely be carried out and through holes may be formed instead of the dimples 53. That is because the adhesion strength to the molding resin 8 can be improved by through